Digital Transistors (BRT) R1 = 100 kΩ, R2 = ∞ kΩ

PNP Transistors with Monolithic Bias Resistor Network

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base–emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

Features

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (T_A = 25°C)

Rating	Symbol	Max	Unit	
Collector-Base Voltage	V_{CBO}	50	Vdc	
Collector-Emitter Voltage	V _{CEO}	50	Vdc	
Collector Current – Continuous	I _C	100	mAdc	
Input Forward Voltage	$V_{IN(fwd)}$	40	Vdc	
Input Reverse Voltage	V _{IN(rev)}	5	Vdc	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

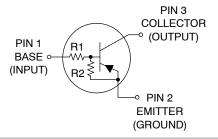
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ON Semiconductor®

http://onsemi.com

PIN CONNECTIONS



MARKING DIAGRAM



X M 1

SOT-1123 CASE 524AA STYLE 1

XXX = Specific Device Code

M = Date Code*
■ Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

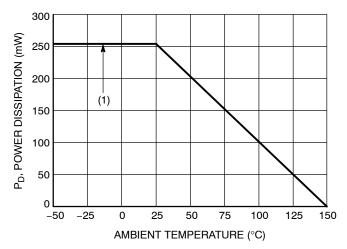
See detailed ordering, marking, and shipping information in the package dimensions section on page 2 of this data sheet.

Table 1. ORDERING INFORMATION

Device	Part Marking	Package	Shipping [†]
NSBA115TF3T5G	Q (90°)*	SOT-1123	8,000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

* (xx°) = Degree rotation in the clockwise direction.



(1) SOT-1123; 100 mm², 1 oz. copper trace

Figure 1. Derating Curve

Table 2. THERMAL CHARACTERISTICS

Characteristic		Symbol	Max	Unit
THERMAL CHARACTERISTICS (SOT-1123) (NSBA115TF3)				
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	(Note 1) (Note 2) (Note 1) (Note 2)	P _D	254 297 2.0 2.4	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ hetaJA}$	493 421	°C/W
Thermal Resistance, Junction to Lead	(Note 1)	$R_{ heta JL}$	193	°C/W
Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +150	°C

^{1.} FR-4 @ 100 mm 2 , 1 oz. copper traces, still air. 2. FR-4 @ 500 mm 2 , 1 oz. copper traces, still air.

Table 3. ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$, unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	•	•			
Collector–Base Cutoff Current $(V_{CB} = 50 \text{ V}, I_E = 0)$	Ісво	_	_	100	nAdc
Collector–Emitter Cutoff Current (V _{CE} = 50 V, I _B = 0)	I _{CEO}	-	-	500	nAdc
Emitter-Base Cutoff Current (V _{EB} = 6.0 V, I _C = 0)	I _{EBO}	_	_	0.1	mAdc
Collector-Base Breakdown Voltage $(I_C = 10 \mu A, I_E = 0)$	V _(BR) CBO	50	-	_	Vdc
Collector–Emitter Breakdown Voltage (Note 3) (I _C = 2.0 mA, I _B = 0)	V _(BR) CEO	50	-	_	Vdc
ON CHARACTERISTICS	•				
DC Current Gain (Note 3) (I _C = 5.0 mA, V _{CE} = 10 V)	h _{FE}	160	350	-	
Collector-Emitter Saturation Voltage (Note 3) (I _C = 10 mA, I _B = 0.3 mA)	V _{CE(sat)}	_	_	0.25	Vdc
Input Voltage (off) (V _{CE} = 5.0 V, I _C = 100 μ A)	V _{i(off)}	-	0.62	-	Vdc
Input Voltage (on) (V _{CE} = 0.2 V, I _C = 1.0 mA)	V _{i(on)}	_	1.0	-	Vdc
Output Voltage (on) ($V_{CC} = 5.0 \text{ V}, V_B = 2.5 \text{ V}, R_L = 1.0 \text{ k}\Omega$)	V _{OL}	-	-	0.2	Vdc
Output Voltage (off) $(V_{CC} = 5.0 \text{ V}, V_B = 0.5 \text{ V}, R_L = 1.0 \text{ k}\Omega)$	V _{OH}	4.9	_	_	Vdc
Input Resistor	R1	70	100	130	kΩ
Resistor Ratio	R ₁ /R ₂	-	-	-	

^{3.} Pulsed Condition: Pulse Width = 300 msec, Duty Cycle ≤ 2%.

TYPICAL CHARACTERISTICS - NSBA115TF3

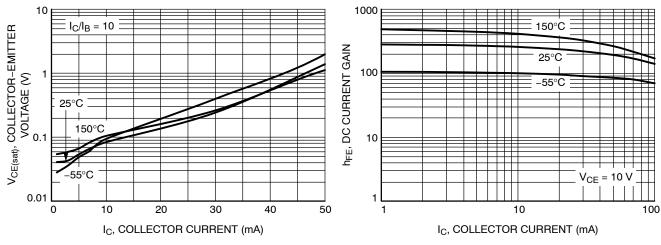


Figure 2. V_{CE(sat)} vs. I_C

Figure 3. DC Current Gain

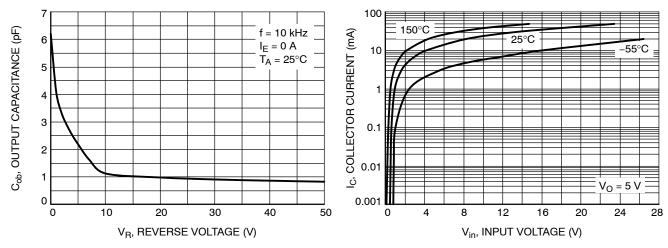


Figure 4. Output Capacitance

Figure 5. Output Current vs. Input Voltage

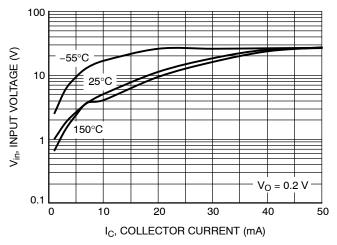
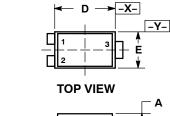
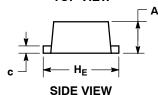


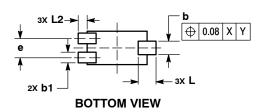
Figure 6. Input Voltage vs. Output Current

PACKAGE DIMENSIONS

SOT-1123 CASE 524AA ISSUE C







NOTES:

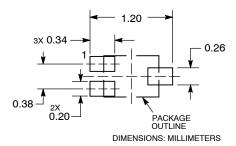
- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS

	MILLIMETERS		
DIM	MIN	MAX	
Α	0.34	0.40	
b	0.15	0.28	
b1	0.10	0.20	
С	0.07	0.17	
D	0.75	0.85	
Е	0.55	0.65	
е	0.35	0.40	
HE	0.95	1.05	
L	0.185 REF		
12	0.05	0.15	

STYLE 1: PIN 1. BASE 2. EMITTER

3. COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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